Product data sheet

1. General description

Ultrafast power diode in a SOD142 (2-lead TO247) plastic package.

2. Features and benefits

- Fast switching
- Low forward voltage drop
- Low thermal resistance
- Soft recovery characteristic
- Reduces switching losses in associated MOSFET or IGBT
- · Planar passivated for voltage ruggedness and reliability

3. Applications

- Switched-Mode Power Supplies
- Power factor correction diode
- Uninterrupted Power Supply
- · Motor drive and SMPS freewheeling diode

4. Quick reference data

Table 1. Quick reference data

| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit |
|-------------------------|---------------------------------|--|--|-----|-----|------|------|
| V_{RRM} | repetitive peak reverse voltage | | | - | - | 1200 | V |
| I _{F(AV)} | average forward current | δ = 0.5; T _{mb} ≤ 98 °C; square-wave pulse; Fig. 1; Fig. 2; Fig. 3 | | - | - | 16 | A |
| Static charact | eristics | | | | | | |
| V _F | forward voltage | I _F = 16 A; T _j = 125 °C; <u>Fig. 6</u> | | - | 1.8 | 2.7 | V |
| Dynamic characteristics | | | | | | | |
| t _{rr} | reverse recovery time | $I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 100 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$ | | - | 50 | - | ns |





5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline | Graphic symbol |
|-----|--------|-------------------------------------|--------------------|----------------|
| 1 | K | cathode | | K — A |
| 2 | Α | anode | | 001aaa020 |
| mb | mb | mounting base; connected to cathode | TO-247 (SOD142) | |

6. Ordering information

Table 3. Ordering information

| Type number | | Package | | | | | |
|-------------|-------------|---------|---|---------|--|--|--|
| | | Name | Description | Version | | | |
| | BYR16W-1200 | TO-247 | Plastic Single-ended through-hole package; Heatsink mounted; 1 mounting hole; 2-lead TO-247 | SOD142 | | | |

7. Marking

Table 4. Marking codes

| Type number | Marking code |
|-------------|--------------|
| BYR16W-1200 | BYR16W-1200 |

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | Min | Max | Unit |
|--------------------|---------------------------------|--|-----|------|------|
| V_{RRM} | repetitive peak reverse voltage | | - | 1200 | V |
| V_{RWM} | crest working reverse voltage | | - | 1200 | V |
| V _R | reverse voltage | DC | - | 1200 | V |
| I _{F(AV)} | average forward current | δ = 0.5; T _{mb} ≤ 98 °C; square-wave pulse; Fig. 1; Fig. 2; Fig. 3 | - | 16 | А |
| I _{FRM} | repetitive peak forward current | $δ = 0.5$; $t_p = 25 \mu s$; $T_{mb} \le 98 °C$; square-wave pulse | - | 32 | А |

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| Symbol | Parameter | Conditions | Min | Max | Unit |
|------------------|-------------------------------------|--|-----|-----|------|
| I _{FSM} | non-repetitive peak forward current | t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; <u>Fig. 4</u> | - | 150 | A |
| | | t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4 | - | 165 | A |
| T _{stg} | storage temperature | | -55 | 150 | °C |
| T _j | junction temperature | | - | 150 | °C |

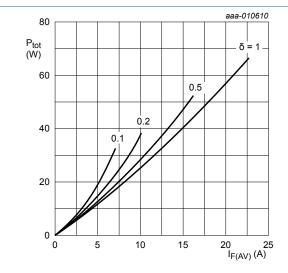


Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values

$$\begin{split} I_{\textit{F(AV)}} = I_{\textit{F(RMS)}} \times \sqrt{\delta} \\ V_{\text{O}} = 2.210 \text{ V; R}_{\text{S}} = 0.032 \text{ } \Omega \end{split}$$

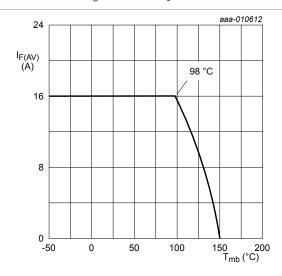


Fig. 3. Forward current as a function of mounting base temperature; maximum values

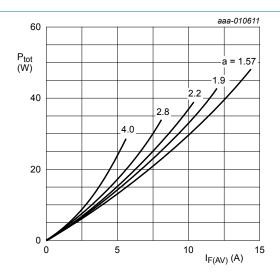


Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

a = form factor =
$$I_{F(RMS)}/I_{F(AV)}$$

 V_{\odot} = 2.210 V; R_{S} = 0.032 Ω

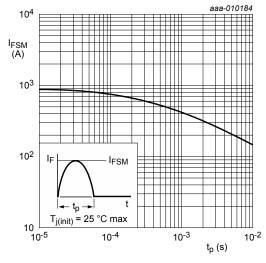
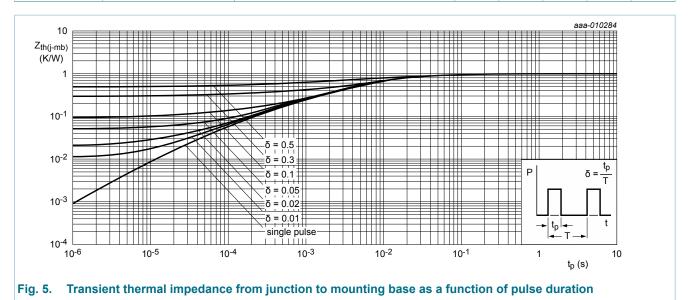


Fig. 4. Non-repetitive peak forward current as a function of pulse width; sinusoidal waveform; maximum values

9. Thermal characteristics

Table 6. Thermal characteristics

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|-----------------------|---|--------------------------------|-----|-----|-----|------|
| R _{th(j-mb)} | thermal resistance from junction to mounting base | with heatsink compound; Fig. 5 | - | - | 1 | K/W |
| R _{th(j-a)} | thermal resistance from junction to ambient | in free air | - | 45 | - | K/W |



10. Characteristics

Table 7. Characteristics

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|---------------------------------|--|---|-----|------|--------------|----------------|
| Static char | acteristics | | | | | |
| V _F | forward voltage | I _F = 16 A; T _j = 25 °C; <u>Fig. 6</u> | - | 2.3 | 3 | V |
| | | I _F = 32 A; T _j = 25 °C; <u>Fig. 6</u> | - | 2.8 | 3.9 | V |
| | | I _F = 16 A; T _j = 125 °C; <u>Fig. 6</u> | - | 1.8 | 2.7 | V |
| I _R | reverse current | V _R = 1200 V; T _j = 25 °C | - | 3 | 100 | μA |
| | | V _R = 1200 V; T _j = 125 °C | - | 0.2 | 2 | mA |
| Dynamic cl | naracteristics | | | | | |
| Q _r recovered charge | | $I_F = 16 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/$ μ s; $T_j = 25 ^{\circ}\text{C}; Fig. 7$ | - | 520 | - | nC |
| | | $I_F = 16 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/$ μ s; $T_j = 125 \text{ °C}; Fig. 7$ | - | 1200 | - | nC |
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| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|-----------------|-------------------------------|---|-----|------|-----|------|
| | | $I_F = 16 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 200 \text{ A/}$ $\mu s; T_j = 25 \text{ °C}; Fig. 7$ | - | 605 | - | nC |
| | | $I_F = 16 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 200 \text{ A/}$ $\mu s; T_j = 125 \text{ °C}; Fig. 7$ | - | 1600 | - | nC |
| t _{rr} | reverse recovery time | $I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 200 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$ | - | 40 | - | ns |
| | | $I_F = 16 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/$ $\mu s; T_j = 25 \text{ °C}; Fig. 7$ | - | 90 | - | ns |
| | | $I_F = 16 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/$ $\mu s; T_j = 125 \text{ °C}; Fig. 7$ | - | 150 | - | ns |
| | | $I_F = 16 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 200 \text{ A/}$ $\mu s; T_j = 25 ^{\circ}\text{C}; Fig. 7$ | - | 105 | - | ns |
| | | $I_F = 16 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 200 \text{ A/}$ $\mu s; T_j = 125 \text{ °C}; Fig. 7$ | - | 200 | - | ns |
| | | $I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 100 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$ | - | 50 | - | ns |
| RM | peak reverse recovery current | I_F = 16 A; V_R = 200 V; dI_F/dt = 200 A/ μ s; T_j = 25 °C; <u>Fig. 7</u> | - | 11.2 | - | Α |
| | | I_F = 16 A; V_R = 200 V; dI_F/dt = 200 A/ μ s; T_j = 125 °C; <u>Fig. 7</u> | - | 16 | - | A |
| | | I_F = 16 A; V_R = 400 V; dI_F/dt = 200 A/ μ s; T_j = 25 °C; $Fig. 7$ | - | 11.2 | - | A |
| | | $I_F = 16 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 200 \text{ A}/$ μ s; $T_j = 125 \text{ °C}; Fig. 7$ | - | 16.2 | - | A |

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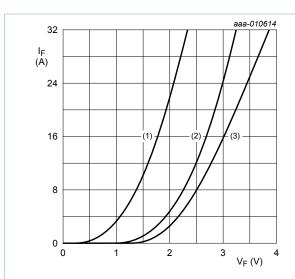


Fig. 6. Forward current as a function of forward voltage

(1) $T_j = 125$ °C; typical values;

(2) $T_j = 125$ °C; maximum values;

(3) $T_j = 25$ °C; maximum values;

 $V_{O} = 2.210 \text{ V}; R_{S} = 0.032 \Omega$

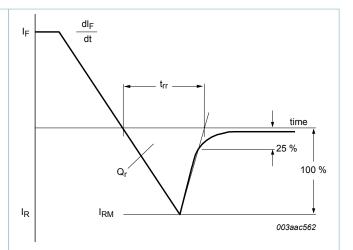
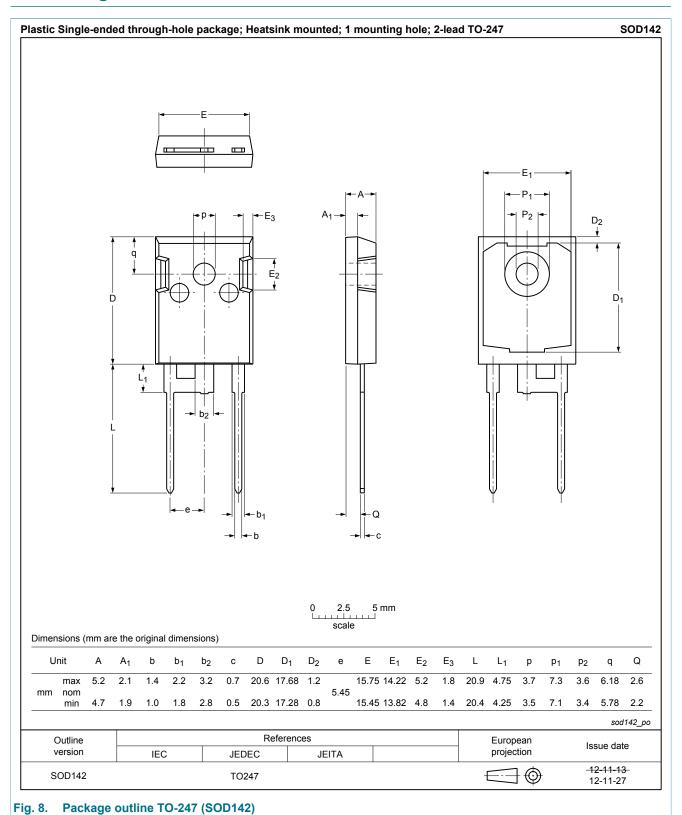


Fig. 7. Reverse recovery definitions; ramp recovery

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11. Package outline



12. Legal information

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